

Abstract

A package substrate free of malfunction or error even with an IC chip in a high frequency range, particularly an IC chip with a frequency exceeding 3 GHz, is provided. A conductor layer 34P on a core substrate 30 is formed to have a thickness of 30 μm and a conductor circuit 58 on an interlayer resin insulating layer 50 is formed to have a thickness of 15 μm . By making the conductor layer 34P thick, it is possible to increase a volume of the conductor itself and decrease resistance. Further, by employing the conductor layer 34 as a power supply layer, it is possible to improve a capability of supplying power to the IC chip.